

# **N-Channel Power MOSFET**

60V, 3A,  $85m\Omega$ 

#### **FEATURES**

- Low R<sub>DS(ON)</sub> to minimize conductive losses
- Logic level
- Low gate charge for fast power switching
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V <sub>D</sub>	S	60	V	
D (****)	V <sub>GS</sub> = 10V	85	O	
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	100	mΩ	
$Q_{g}$		4.6	nC	

# Pb

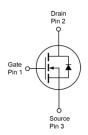




#### **APPLICATIONS**

- BLDC Motor Control
- Battery Power Management
- LED backlight





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		3	Λ.	
	$T_C = 25^{\circ}C$ $T_A = 25^{\circ}C$	l <sub>D</sub>	2.3	Α	
Pulsed Drain Current		I <sub>DM</sub>	12	А	
Total Power Dissipation	$T_C = 25^{\circ}C$	P <sub>D</sub>	1.7	W	
	T <sub>C</sub> = 125°C		0.3	VV	
Total Power Dissipation	$T_A = 25$ °C	$P_{D}$	1	\^/	
	$T_A = 125^{\circ}C$		0.2	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	75	°C/W	
Junction to Ambient Thermal Resistance	R <sub>OJA</sub>	124	°C/W	

**Thermal Performance Note:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.



PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	60			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.2	1.8	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
	$V_{GS} = 0V, V_{DS} = 60V$				1	μA
Drain-Source Leakage Current	Fource Leakage Current $V_{GS} = 0V, V_{DS} = 60V$ $I_{DSS}$ $T_J = 125^{\circ}C$	I <sub>DSS</sub>			100	
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.3A$	_		68	85	mΩ
(Note 2)	$V_{GS} = 4.5V, I_D = 2.3A$	$R_{DS(on)}$		80	100	
Forward Transconductance (Note 2)	$V_{DS} = 5V, I_{D} = 2.3A$	g <sub>fs</sub>		6.7		S
Dynamic (Note 3)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 30V,$ $I_{D} = 2.3A$	$Q_g$		9.5		
Total Gate Charge		$Q_{g}$		4.6		nC
Gate-Source Charge	$V_{GS} = 4.5V, V_{DS} = 30V,$	$Q_{gs}$		1.9		-
Gate-Drain Charge	$I_D = 2.3A$	$Q_{gd}$		1.6		
Input Capacitance		C <sub>iss</sub>		529		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 30V$	C <sub>oss</sub>		29		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		3		
Gate Resistance	f = 1.0MHz	$R_g$		1.5		Ω
Switching (Note 3)						
Turn-On Delay Time		t <sub>d(on)</sub>		4.8		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$ $I_D = 2.3A, R_G = 2\Omega$	t <sub>r</sub>		20		
Turn-Off Delay Time		t <sub>d(off)</sub>		9.8		ns
Turn-Off Fall Time		t <sub>f</sub>		17		
Source-Drain Diode						
Forward Voltage (Note 2)	$V_{GS} = 0V, I_{S} = 2.3A$	$V_{SD}$			1	V
Reverse Recovery Time	I <sub>S</sub> = 2.3A,	t <sub>rr</sub>		12		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q <sub>rr</sub>		8		nC

#### Notes:

- 1. Silicon limited current only.
- 2. Pulse test: Pulse Width ≤ 300µs, duty cycle ≤ 2%.
- 3. Switching time is essentially independent of operating temperature.

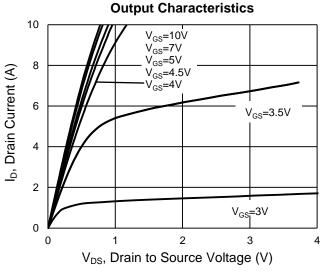
## **ORDERING INFORMATION**

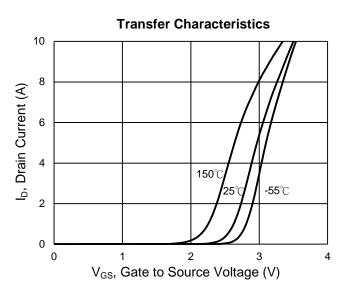
ORDERING CODE	PACKAGE	PACKING
TSM850N06CX RFG	SOT-23	3,000pcs / 7" Reel

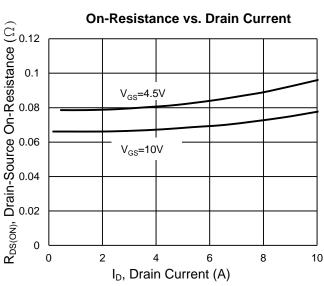


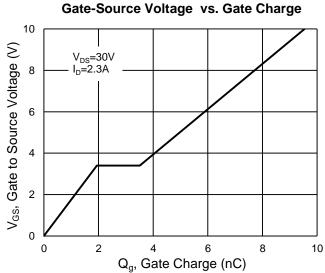
#### **CHARACTERISTICS CURVES**

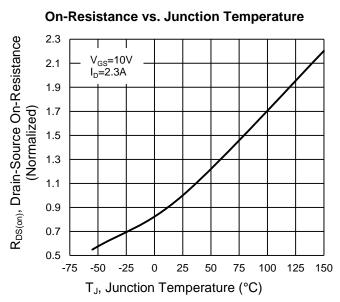
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

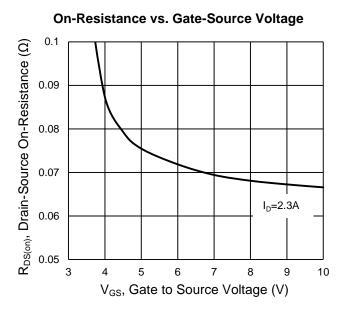












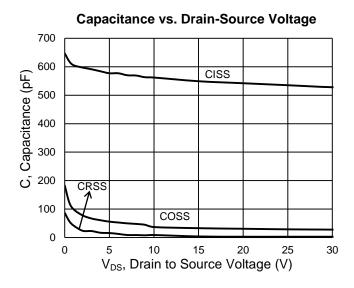
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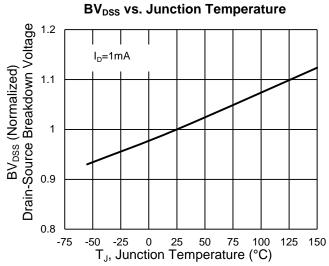
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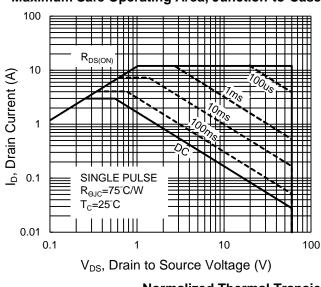
### **CHARACTERISTICS CURVES**

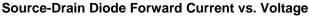
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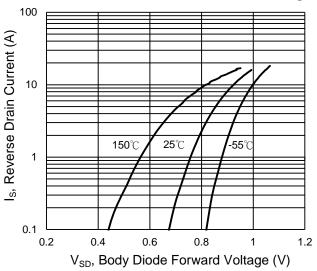




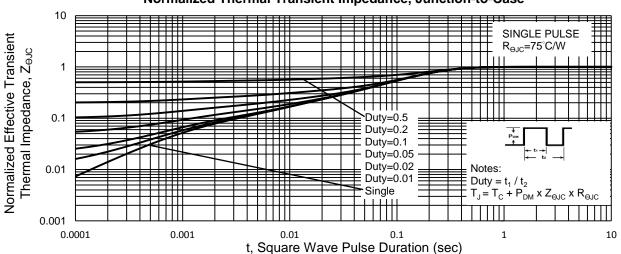
## Maximum Safe Operating Area, Junction-to-Case







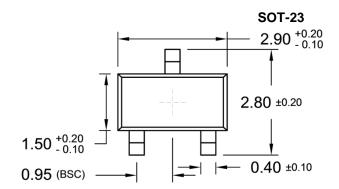
#### Normalized Thermal Transient Impedance, Junction-to-Case

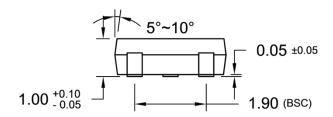


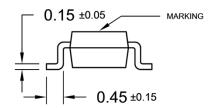
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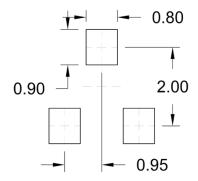
# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







# **SUGGESTED PAD LAYOUT** (Unit: Millimeters)



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## **MARKING DIAGRAM**



**85** = Device Code

Y = Year Code

M = Month Code

 $oldsymbol{O}$  =Jan  $oldsymbol{P}$  =Feb  $oldsymbol{Q}$  =Mar  $oldsymbol{R}$  =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

**L** = Lot Code



Taiwan Semiconductor

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